

L Number	Hits	Search Text	DB	Time Stamp
1	26	reinforcement NEAR means	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 11:59
2	2755	reinforcement NEAR (beam means strip\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 12:11
3	1	(reinforcement NEAR (beam means strip\$1)) and (array\$2 NEAR waveguide NEAR grating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 12:02
4	204	(reinforcement NEAR (beam means strip\$1)) and ((array\$2 NEAR waveguide NEAR grating) chip die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 12:02
5	2	((reinforcement NEAR (beam means strip\$1)) and ((array\$2 NEAR waveguide NEAR grating) chip die)) and (copper NEAR plate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 12:10
6	2	(reinforcement NEAR (beam means strip\$1)) and (copper NEAR plate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:08
7	0	(reinforcement NEAR (beam means strip\$1)) same (copper NEAR plate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 12:11
8	8	(reinforcement NEAR (beam means strip\$1)) same copper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 12:59
9	17	(reinforcement NEAR (beam means strip\$1)) with (chip die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:07
10	2183	reinforcement with (chip die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:08
11	13	(reinforcement with (chip die)) and (copper NEAR plate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:08

L Number	Hits	Search Text	DB	Time stamp
12	177	reinforcement with mount\$3 with (chip die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:18
13	6	(reinforcement with mount\$3 with (chip die)) and (copper NEAR plate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:19
14	26	reinforcement with mount\$3 with ((part portion) NEAR5 (chip die))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:33
15	1	(reinforcement with mount\$3 with ((part portion) NEAR5 (chip die))) and (copper NEAR plate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:35
16	2	(reinforcement with mount\$3 with ((part portion) NEAR5 (chip die))) and copper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:19
17	7	5440171.URPN.	USPAT	2003/03/14 13:21
18	2	("4038488" "5028986").PN.	USPAT	2003/03/14 13:21
19	1286	(reinforcement copper metal) with mount\$3 with ((part portion) NEAR5 (chip die))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:34
21	51	((reinforcement copper metal) with mount\$3 with ((part portion) NEAR5 (chip die))) and (copper NEAR plate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:35
20	129	((copper metal) NEAR plate) with mount\$3 with ((part portion) NEAR5 (chip die))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:42
22	11	(copper NEAR plate) with mount\$3 with ((part portion) NEAR5 (chip die))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 13:43

L Number	Hits	Search Text	DB	Time stamp
1	6717	(first NEAR (chip die)) same (second NEAR (chip die))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:53
2	1046	(first NEAR (chip die)) same (second NEAR (chip die)) same (bond\$3 combin\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:56
3	1079	(first NEAR (chip die wafer)) WITH (second NEAR (chip die wafer)) WITH (bond\$3 combin\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:57
4	170	((first NEAR (chip die wafer)) WITH (second NEAR (chip die wafer)) WITH (bond\$3 combin\$3)) and (concave hollow\$ curv\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:20
5	91	(((first NEAR (chip die wafer)) WITH (second NEAR (chip die wafer)) WITH (bond\$3 combin\$3)) and (concave hollow\$ curv\$3)) and (cut\$4 dic\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:19
6	469	((first NEAR (chip die wafer)) WITH (second NEAR (chip die wafer)) WITH (bond\$3 combin\$3)) and (cut\$4 dic\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:10
7	245	(((first NEAR (chip die wafer)) WITH (second NEAR (chip die wafer)) WITH (bond\$3 combin\$3)) and (cut\$4 dic\$3)) and adhesive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:11
8	1	(((first NEAR (chip die wafer)) WITH (second NEAR (chip die wafer)) WITH (bond\$3 combin\$3)) and (cut\$4 dic\$3)) and adhesive) and (purity NEAR level)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:25
9	1	((first NEAR (chip die wafer)) WITH (second NEAR (chip die wafer)) WITH (bond\$3 combin\$3)) and (purity NEAR level)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:19
10	245	(((first NEAR (chip die wafer)) WITH (second NEAR (chip die wafer)) WITH (bond\$3 combin\$3)) and (cut\$4 dic\$3)) and adhesive) and (cut\$4 dic\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:19
11	35	((((first NEAR (chip die wafer)) WITH (second NEAR (chip die wafer)) WITH (bond\$3 combin\$3)) and (cut\$4 dic\$3)) and adhesive) and (cut\$4 dic\$3)) and (concave curv\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:20
12	4122	(purity NEAR level)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:25

13	1101	((purity NEAR level)) and (Si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:25
14	104	(silicon Si) WITH (purity NEAR level)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:36
15	40	((silicon Si) WITH (purity NEAR level)) and wafer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:26
16	1	((first second) NEAR wafer\$1) and (silicon Si) WITH (purity NEAR level)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:32
17	0	((first second) NEAR wafer\$1) WITH (silicon Si) WITH (purity NEAR level)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:33
18	12382	((first second) NEAR wafer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:37
19	9	((((first second) NEAR wafer\$1)) and ((silicon Si) same (purity NEAR level)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:35
20	1	((((first second) NEAR wafer\$1)) and ((silicon Si) WITH (purity NEAR level)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:35
21	213	(silicon Si) same (purity NEAR level)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:36
22	9	((silicon Si) same (purity NEAR level)) and (((first second) NEAR wafer\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:39
23	2080	(first NEAR wafer\$1) WITH (second NEAR wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:55
24	3	((first NEAR wafer\$1) WITH (second NEAR wafer)) and ((silicon Si) same (purity NEAR level))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:38
25	76	((silicon Si) same (purity NEAR level)) and wafer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 17:39

26	18	((first NEAR chip) WITH (second NEAR chip)) and ((first NEAR wafer) WITH (second NEAR wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 18:04
27	9	((first NEAR chip) WITH (second NEAR chip)) same ((first NEAR wafer) WITH (second NEAR wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 18:04

L Number	Hits	Search Text	DB	Time stamp
1	1642	257/620,622.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 08:48
2	744	257/620,622.ccls. and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 08:49
3	127	(257/620,622.ccls. and (chip die wafer)) and (concave hollow\$2 curv\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 09:55
4	377	(257/620,622.ccls. and (chip die wafer)) and (dic\$3 cut\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 09:56
5	244	((257/620,622.ccls. and (chip die wafer)) and (dic\$3 cut\$4)) and (arrang\$5 lay-out configur\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 09:56
6	135	(((257/620,622.ccls. and (chip die wafer)) and (dic\$3 cut\$4)) and (arrang\$5 lay-out configur\$5)) and shape	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 09:55
7	0	6521513.URPN.	USPAT	2003/03/14 09:19
8	12	("4925808" "4984358" "5501893" "5656547" "5668400" "5753959" "5814885" "5904546" "5910687" "5928526" "6306731" "6387778").PN.	USPAT	2003/03/14 09:19
9	23	5341024.URPN.	USPAT	2003/03/14 09:46
10	16	("4816692" "5305222" "5341024" "5404309" "5416722" "5450332" "5532934" "5553273" "5581475" "5612893" "5636131" "5663076" "5684713" "5699260" "5822214" "5838567").PN.	USPAT	2003/03/14 09:47
11	1	6021267.URPN.	USPAT	2003/03/14 09:48
12	23	5341024.URPN.	USPAT	2003/03/14 09:49
13	22049	wafer\$1 WITH shape\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 09:55
14	6213	(wafer\$1 WITH shape\$1) and (concave hollow\$2 curv\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:01
15	2882	((wafer\$1 WITH shape\$1) and (concave hollow\$2 curv\$3)) and (dic\$3 cut\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:00
16	2446	(((wafer\$1 WITH shape\$1) and (concave hollow\$2 curv\$3)) and (dic\$3 cut\$4)) and (arrang\$5 lay-out configur\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:01

17	323	((((wafer\$1 WITH shape\$1) and (concave hollow\$2 curv\$3)) and (dic\$3 cut\$4)) and (arrang\$5 lay-out configur\$5)) and (substrate NEAR material\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:02
18	3	((((wafer\$1 WITH shape\$1) and (concave hollow\$2 curv\$3)) and (dic\$3 cut\$4)) and (arrang\$5 lay-out configur\$5)) and (substrate NEAR material\$1)) and (waveguide NEAR grating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:02
19	26418	wafer\$1 WITH (dic\$3 cut\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:00
20	510	((wafer\$1 WITH (dic\$3 cut\$4)) and ((concave hollow\$2 curv\$3) NEAR shape\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:01
21	430	((wafer\$1 WITH (dic\$3 cut\$4)) and ((concave hollow\$2 curv\$3) NEAR shape\$1)) and (arrang\$5 lay-out configur\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:01
23	1	((((wafer\$1 WITH (dic\$3 cut\$4)) and ((concave hollow\$2 curv\$3) NEAR shape\$1)) and (arrang\$5 lay-out configur\$5)) and (substrate NEAR material\$1)) and (waveguide NEAR grating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:02
22	86	((((wafer\$1 WITH (dic\$3 cut\$4)) and ((concave hollow\$2 curv\$3) NEAR shape\$1)) and (arrang\$5 lay-out configur\$5)) and (substrate NEAR material\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:03
24	0	6193585.URPN.	USPAT	2003/03/14 10:16
25	18	("4836881" "4863529" "5071785" "5240749" "5241140" "5270028" "5270077" "5273731" "5294381" "5382809" "5584045" "5587013" "5736226" "5776246" "5855998" "5874130" "5964942" "6051063").PN.	USPAT	2003/03/14 10:16